OXFORD INSTRUMENTS

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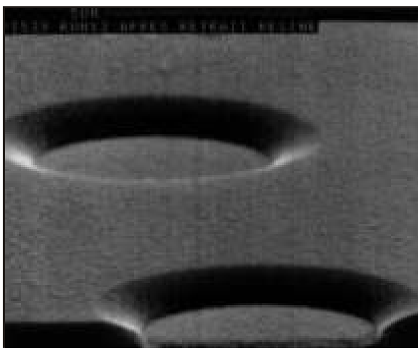
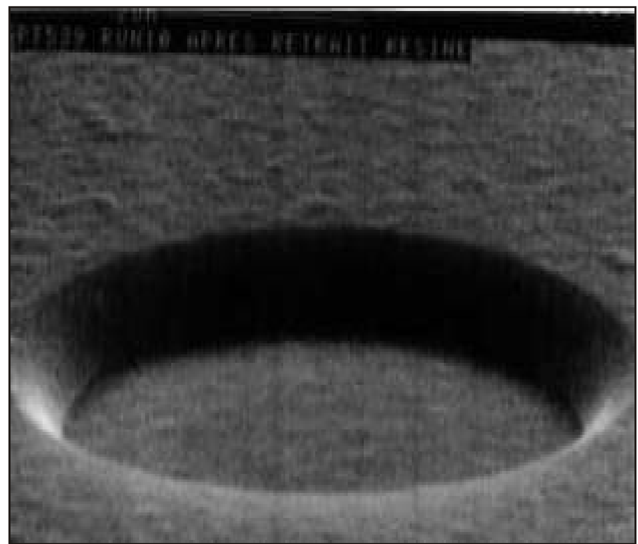
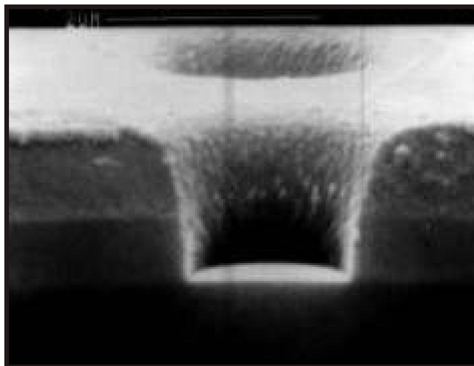
Plasmalab Data

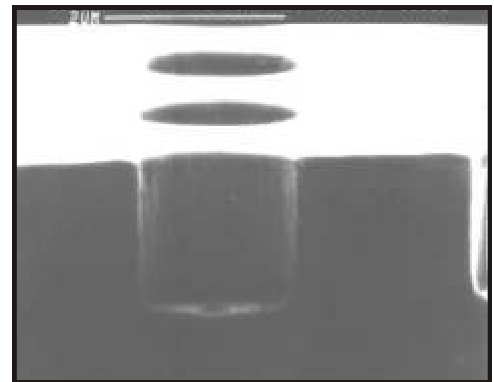
SiO_2 Via Hole Etching



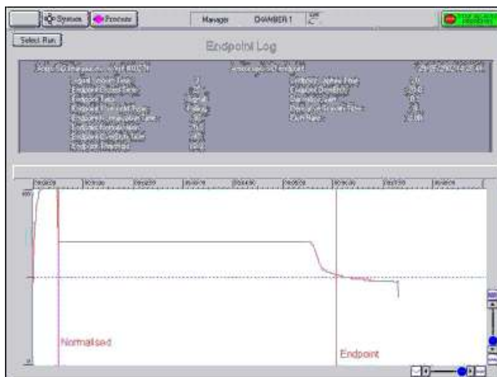




2 µm deep etch of shaped via holes into SiO_2 for reliable metallisation



Anisotropic etch:
PR in pace (rhs)
and removed (lhs)



Signal from
optical emission

Rate : ca. 25 - 100 nm/min*
Mask: Photoresist
Selectivity to PR mask: 3 - 10:1
Selectivity to Si: 8 - 20:1
Profil: controllable (30° - 90°)
Uniformity: +/- 3 %
*High rates require Helium cooling, if a PR mask is used.
Even higher rates are possible with hard masks.

Plasmalab 80 Plus
Plasmalab 800 Plus
Plasmalab System 100
Plasmalab System 133